

**RoHS** 

COMPLIANT

# Phase Control Thyristors (Stud Version), 200 A



PRIMARY CHARACTERISTICS			
I <sub>T(AV)</sub>	200 A		
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V, 2000 V		
V <sub>TM</sub>	1.75 V		
I <sub>GT</sub>	150 mA		
T <sub>J</sub>	-40 °C to +125 °C		
Package	TO-93 (TO-209AB)		
Circuit configuration	Single SCR		

#### **FEATURES**

- Center amplifying gate
- International standard case TO-93 (TO-209AB))
- Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- · DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		200	A		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		314	Α		
	50 Hz	5000			
ITSM	60 Hz	5230	A		
l²t	50 Hz	125	1.42-		
	60 Hz	114	kA <sup>2</sup> s		
V <sub>DRM</sub> /V <sub>RRM</sub>		1600 to 2000	V		
tq	Typical	100	μs		
T <sub>J</sub>		-40 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
VC CT100C	16	1600	1700	30				
VS-ST180S 20		2000	2100	30				



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I <sub>T(AV)</sub>	180° condu	180° conduction, half sine wave		200 85	A °C
Maximum RMS on-state current	I-(D. 40)	DC at 76 °C	case temperat	UΓΑ	314	
Maximum rivio on-state current	I <sub>T(RMS)</sub>		· · · · · · · · · · · · · · · · · · ·	ure I		
		t = 10 ms	No voltage		5000	A kA <sup>2</sup> s
Maximum peak, one-cycle	$I_{TSM}$	t = 8.3  ms	reapplied		5230	
non-repetitive surge current	TISM	t = 10 ms	100 % V <sub>RRM</sub>		4200	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	4400	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage		125	
		t = 8.3 ms	reapplied		114	
		t = 10 ms	100 % V <sub>RRM</sub>		88	
		t = 8.3 ms	reapplied		81	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	ms, no voltage	reapplied	1250	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x \mid_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	1.08	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			]
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		1.18	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.14	11152	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 570 \text{ A}, T_J = 125 ^{\circ}\text{C}, t_p = 10 \text{ ms sine pulse}$		1.75	V	
Maximum holding current	I <sub>H</sub>	T T was in an analysis and 40 V with a land		600	mA	
Maximum (typical) latching current	ΙL	$T_J = T_J$ maximum, anode supply 12 V resistive load 1000 (		1000 (300)	IIIA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t <sub>q</sub>	$I_{TM} = 300 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 20 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate } 0 \text{ V } 100 \Omega, t_p = 500 \mu\text{s}$	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA



TRIGGERING							
DADAMETED	CVMPOL	_	TEST CONDITIONS		VALUES		
PARAMETER	SYMBOL	'			MAX.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J \text{ maximum},$	t <sub>p</sub> ≤ 5 ms	1	0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J \text{ maximum},$	f = 50 Hz, d% = 50	2	.0	VV	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T. T. marrianum + < F. ma		7		0	V
Maximum peak negative gate voltage	- V <sub>GM</sub>	ıj = ıjınaxımum,	$T_J = T_J$ maximum, $t_p \le 5$ ms		5.0		
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		180	=.		
DC gate current required to trigger		$I_{GT}$	T <sub>J</sub> = 25 °C	Maximum required gate trigger/	90	150	mA
		T <sub>J</sub> = 125 °C	current/voltage are the lowest value which will trigger all units	40	-		
		T <sub>J</sub> = - 40 °C		2.9	=.		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V	
		T <sub>J</sub> = 125 °C	1	1.2	=.		
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/voltage	1	0	mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to +125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to +150		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.105	IZ AAZ	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	Mounting surface, smooth, flat and greased	0.04	- K/W	
Mounting touris 1100/		Non-lubricated threads	31 (275)	N·m	
Mounting torque, ± 10 %		Lubricated threads	24.5 (210)	(lbf · in)	
Approximate weight			280	g	
Case style		See dimensions - link at the end of datasheeet	TO-93 (TO-209AB)		

$\Delta R_{thJC}$ CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.015	0.012		
120°	0.019	0.020		
90°	0.025	0.027	$T_J = T_J$ maximum	K/W
60°	0.036	0.037		
30°	0.060	0.060		

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

#### www.vishay.com

## Vishay Semiconductors

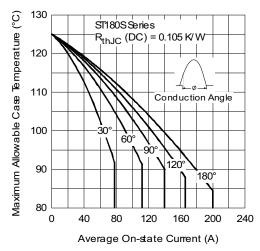


Fig. 1 - Current Ratings Characteristics

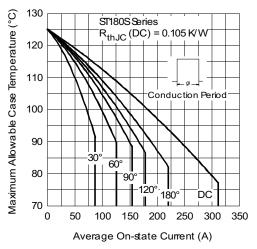


Fig. 2 - Current Ratings Characteristics

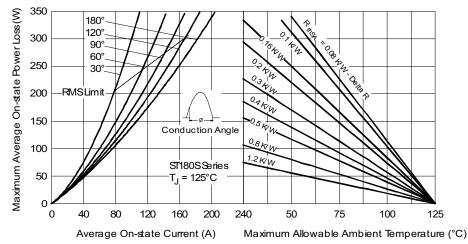


Fig. 3 - On-State Power Loss Characteristics

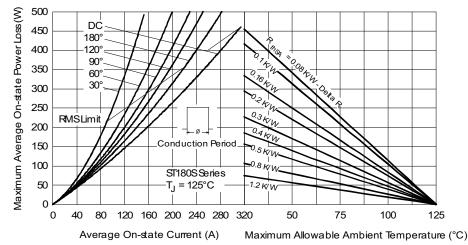


Fig. 4 - On-State Power Loss Characteristics

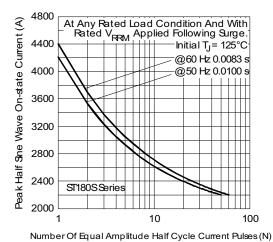


Fig. 5 - Maximum Non-Repetitive Surge Current

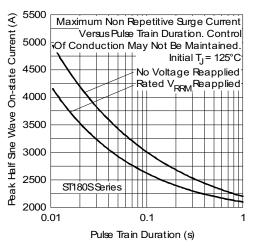


Fig. 6 - Maximum Non-Repetitive Surge Current

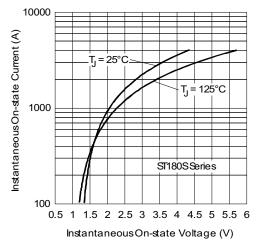


Fig. 7 - On-State Voltage Drop Characteristics

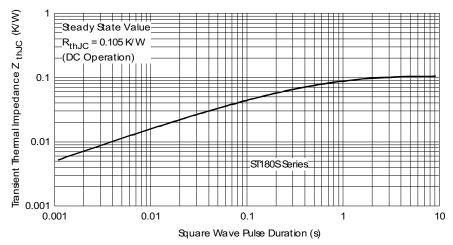


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

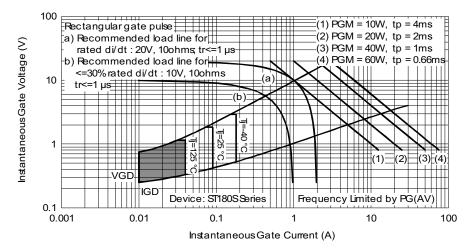
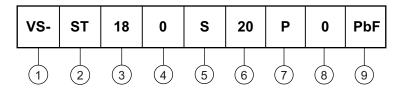


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



Vishay Semiconductors product

2 - Thyristor

Essential part number

4 - 0 = converter grade

5 - S = compression bonding stud

Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - P = stud base 3/4"-16UNF2A threads

8 - 0 = eyelet terminals (gate and auxiliary cathode leads)

1 = fast-on terminals (gate and auxiliary cathode leads)

9 - None = standard production

PbF = lead (Pb)-free

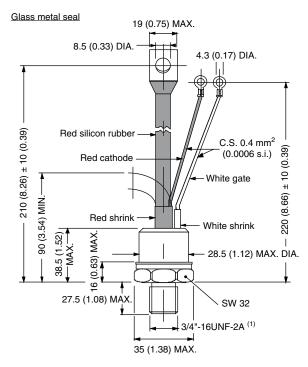
Note: For metric device M16 x 1.5 contact factory

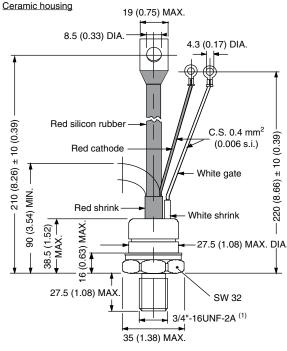
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95082		

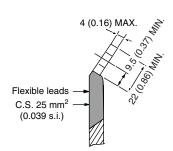


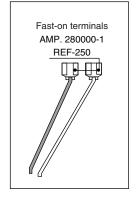
# TO-209AB (TO-93)

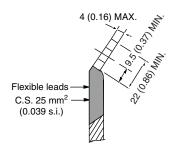
### **DIMENSIONS** in millimeters (inches)











#### Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



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